SILICON CARBIDE (SiC) SCHOTTKY DIODE



SML10SIC06SMDC

- Hermetic Ceramic Surface Mount Package.
- Semelab's Silicon Carbide (SiC) Schottky diodes exhibit low forward voltage and superb high temperature performance.
- Suitable for high-frequency hard switching applications, where system efficiency and reliability are paramount.
- No reverse recovery time due to absence of minority carrier injection.
- Screening Options Available.



ABSOLUTE MAXIMUM RATINGS (Per Diode, T_C = 25°C unless otherwise stated)

VR	DC Reverse Voltage	600V
V_{RRM}	Repetitive Peak Reverse Voltage	600V
lF	DC Forward Current (T _J = 175°C)	10A
IFRM	Repetitive Peak Forward Current (1)	67A
I _{FSM}	Surge Peak Forward Current (2)	250A
P_{D}	Total Power Dissipation at	100W
	Derate Above 25°C	0.5W/°C
TJ	Junction Temperature Range	-55 to +225°C
T_{stg}	Storage Temperature Range	-55 to +225°C

THERMAL PROPERTIES

Symbols	Parameters	Max.	Units
R _{θJC}	Thermal Resistance, Junction To Case	2.0	°C/W

(1) $T_c = 25$ °C, $T_p = 10$ ms, Half Sine Wave, D = 0.3

(2) $T_c = 25^{\circ}C$, $T_c = 10\mu s$



Website: http://www.semelab-tt.com

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ELECTRICAL CHARACTERISTICS (Per Diode, T_C = 25°C unless otherwise stated)

Static Characteristics

Symbols	Parameters	Test Conditions	Min.	Тур.	Max.	Units
V _F	Forward Voltage	I _F = 10A		1.5	1.8	- V
		T _J = 175°C		2.0	2.4	
I _R	Reverse Current	V _R = 600V		10	50	
		T _J = 175°C		20	200	μΑ

Dynamic Characteristics

Q _C	Total Capacitive Charge	$V_{R} = 600V, I_{F} = 10A$ $\delta i / \delta t = 500A / \mu s$	25		nC
С	Total Capacitance	$V_R = 1.0V, f = 1.0MHz$	480		pF
		V _R = 200V, f = 1.0MHz	50		
		V _R = 400V, f = 1.0MHz	42		

MECHANICAL DATA

Dimensions in mm (inches)

